# 陳敏璋教授近五年之著作目錄

## 國際學術期刊論文

1. Sheng-Han Yi, Yu-Chen Chan, Chi-Lin Mo, Hsin-Chih Lin, and Miin-Jang Chen*, "Enhancement of Energy Storage for Electrostatic Supercapacitors through Built-in Electric Field Engineering," *Nano Energy*, 99, 107342, 2022.
2. Chun-Yi Chou, Hsing-Yang Chen, Yu-Sen Jiang, Hsin-Chih Lin, and Miin-Jang Chen*, "Wake-up free $Hf_{0.5}Zr_{0.5}O_2$ thin film with enhanced ferroelectricity and reliability synthesized by atomic layer crystallization induced by substrate biasing," *Acta Materialia*, 228, 117762, 2022.
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## 國際會議論文

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